



N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I _D (A) ^a	Q _g (Typ.)						
100	0.083 at V _{GS} = 10 V	11.3	3.5 nC						
	0.130 at V _{GS} = 4.5 V	9	3.5 110						

PowerPAK SC-70-6L-Single 2.05 mm **Bottom View**

Ordering Information: SiA416DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

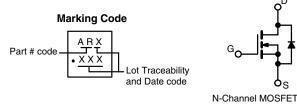
- TrenchFET® Power MOSFET
- 100 % R_q and UIS Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



COMPLIANT HALOGEN FREE

APPLICATIONS

- DC/DC Converters
- Full-Bridge Converters
- For Power Bricks and POL Power





ABSOLUTE MAXIMUM RATINGS	(T _A = 25 °C, unle	ess otherwise	noted)	
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	± 20]
	T _C = 25 °C		11.3	
Continuous Drain Current (T _J = 150 °C)	T _C = 70 °C	1 .	9	1
Continuous Diam Current (1) = 130 °C)	T _A = 25 °C	l _D	4.8 ^{b, c}	1
	T _A = 70 °C		3.9 ^{b, c}	1
Pulsed Drain Current (t = 300 μs)	-	I _{DM}	15	A
Continuous Course Drain Diade Current	T _C = 25 °C	ı	12	
Continuous Source-Drain Diode Current	T _A = 25 °C	l _S	2.9 ^{b, c}	
Single Pulse Avalanche Current	1 0.1 ml l	I _{AS}	3	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	0.45	mJ
	T _C = 25 °C		19	
Maximum Davian Disaination	T _C = 70 °C	_	12	w
Maximum Power Dissipation	T _A = 25 °C	P_{D}	3.5 ^{b, c}] vv
	T _A = 70 °C		2.2 ^{b, c}	
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature	e) ^{d, e}		260	1

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient ^{b, f}	ximum Junction-to-Ambient ^{b, f} $t \le 5 s$		28	36	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	5.3	6.5	C/ VV				

Notes:

- a. Based on T_C = 25 °C.
- b. Surface mounted on 1" x 1" FR4 board.
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted									
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static				_		•			
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V, I}_{D} = 250 \mu\text{A}$	100			V			
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		54		mV/°C			
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	5 1		- 4.4		11107			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1.6		3	V			
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA			
Zoro Coto Voltago Droin Current	I	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ			
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10				
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α			
	В	$V_{GS} = 10 \text{ V}, I_D = 3.2 \text{ A}$		0.068	0.083	Ω			
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 2.6 \text{ A}$		0.092	0.130				
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 3.2 \text{ A}$		8		S			
Dynamic ^b				l	l	ı			
Input Capacitance	C _{iss}			295					
Output Capacitance	C _{oss}	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz		92		pF			
Reverse Transfer Capacitance	C _{rss}			16					
· · · · · · · · · · · · · · · · · · ·		V _{DS} = 50 V, V _{GS} = 10 V, I _D = 4.8 A		6.5	10	nC			
Total Gate Charge	Q_g	30 30 2		3.5	5.3				
Gate-Source Charge	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 4.8 \text{ A}$		1.2					
Gate-Drain Charge	Q_{gd}			1.9					
Output Charge	Q _{oss}	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}$		7.6					
Gate Resistance	R_{g}	f = 1 MHz	0.4	1.8	3.6	Ω			
Turn-On Delay Time	t _{d(on)}			5	10				
Rise Time	t _r	$V_{DD} = 50 \text{ V}, R_1 = 12.8 \Omega$		13	25	- - -			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 3.9 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		10	20				
Fall Time	t _f	_		10	20				
Turn-On Delay Time	t _{d(on)}			25	50	ns			
Rise Time	t _r	$V_{DD} = 50 \text{ V, R}_{1} = 12.8 \Omega$		100	200	- - - -			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 3.9 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_q = 1 \Omega$		15	30				
Fall Time	t _f			25	50				
Drain-Source Body Diode Characteristic					<u> </u>				
Continuous Source-Drain Diode Current	Is	T _C = 25 °C			12				
Pulse Diode Forward Current ^a	I _{SM}				15	A			
Body Diode Voltage	V _{SD}	I _S = 3.9 A		0.85	1.2	V			
Body Diode Reverse Recovery Time	t _{rr}	<u> </u>		30	60	ns			
Body Diode Reverse Recovery Charge	Q _{rr}			30	60	nC			
Reverse Recovery Fall Time	t _a	$I_F = 3.9 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		20					
Reverse Recovery Rise Time	t _b	}		10	-	ns			

Notes:

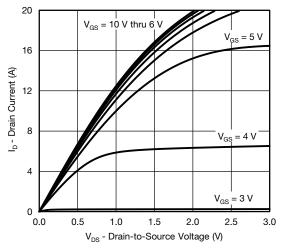
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

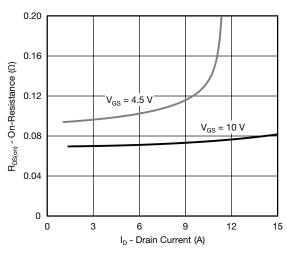
b. Guaranteed by design, not subject to production testing.



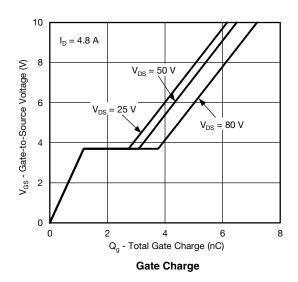
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

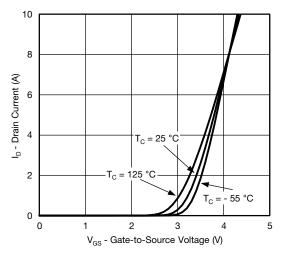


Output Characteristics

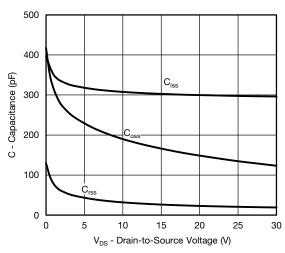


On-Resistance vs. Drain Current and Gate Voltage

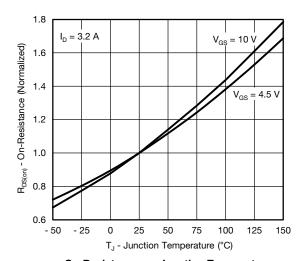




Transfer Characteristics

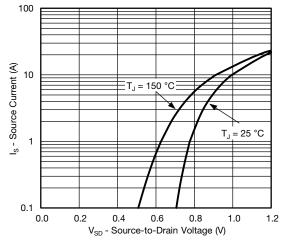


Capacitance

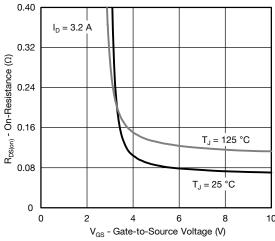


On-Resistance vs. Junction Temperature

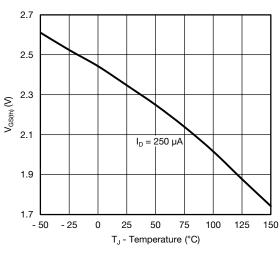
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



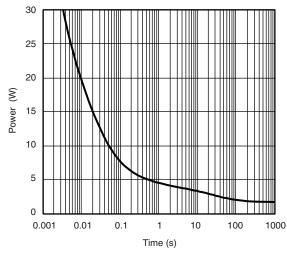
Source-Drain Diode Forward Voltage



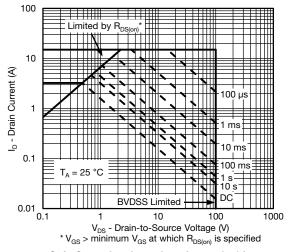
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



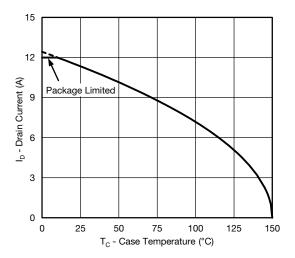
Single Pulse Power, Junction-to-Ambient



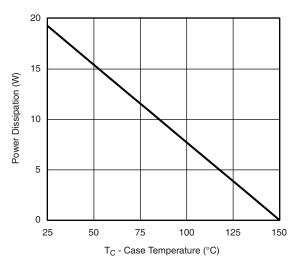
Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*

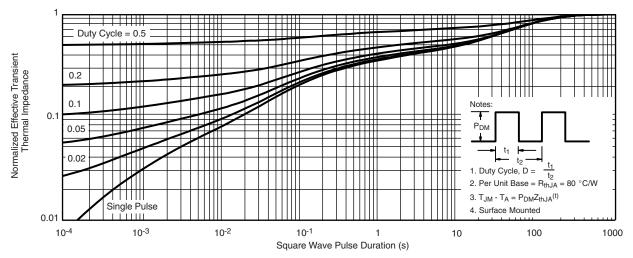


Power, Junction-to-Case

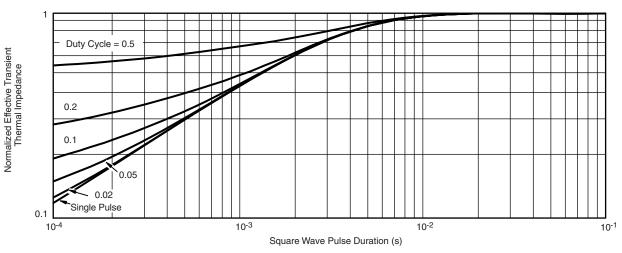
 $^{^{\}star}$ The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg263649.





PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP		0.011 TYP		0.275 TYP			0.011 TYP			
K1		0.400 TYP		0.016 TYP		0.320 TYP			0.013 TYP			
K2		0.240 TYP		0.009 TYP		0.252 TYP			0.010 TYP			
К3		0.225 TYP		0.009 TYP					•	•		
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006

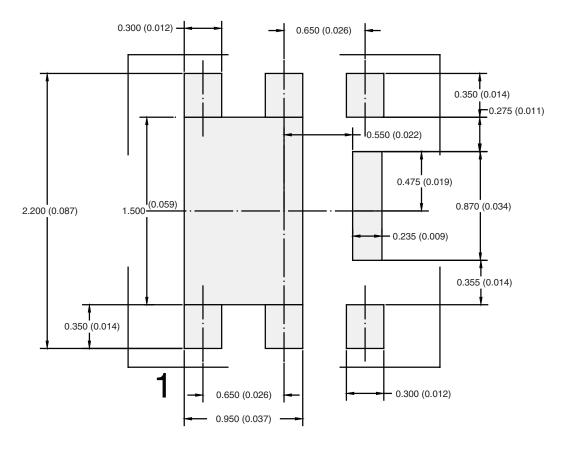
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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